#### TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

# 2 S C 5 4 6 4

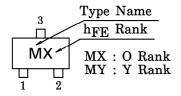
### VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure, High Gain.
- NF=1.1dB,  $|S_{21e}|^2 = 12dB$  (f=1GHz)

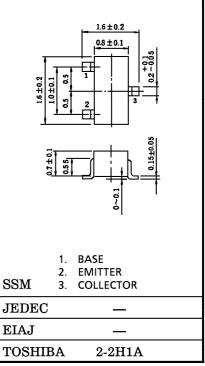
## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	20	V
Collector-Emitter Voltage	$v_{CEO}$	12	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	$I_{\mathbf{C}}$	60	mA
Base Current	$I_{\mathbf{B}}$	30	mA
Collector Power Dissipation	PC	100	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C

#### **MARKING**



### Unit in mm



Weight: 2.4mg

#### MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_{T}$	$V_{CE}=8V, I_{C}=15mA$	5	7	_	GHz
Ilngartion (÷gin	$ S_{21e} ^2$ (1)	$V_{CE} = 8V, I_{C} = 15mA, f = 500MHz$		17.5	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE}=8V$ , $I_{C}=15mA$ , $f=1GHz$	8	12	_	
Noise Figure	NF (1)	$V_{CE}=8V$ , $I_{C}=5mA$ , $f=500MHz$	_	1	_	dB
	NF (2)	$V_{CE}=8V$ , $I_{C}=5mA$ , $f=1GHz$	_	1.1	2	αБ

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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{\mathrm{CBO}}$	$V_{CB} = 10V, I_{E} = 0$	_	_	1	$\mu$ <b>A</b>
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = 1V, I_C = 0$		_	1	$\mu$ A
DC Current Gain	hFE (Note 1)	$V_{\rm CE}$ =8V, $I_{\rm C}$ =15mA	80	_	240	
Output Capacitance	$C_{ob}$	N == - 0		0.8	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	$V_{\mathrm{CB}} = 8V, I_{\mathrm{E}} = 0, f = 1 \mathrm{MHz}$ (Note 2)	I	0.55	_	рF

(Note 1): hFE Classification  $\,$  O : 80~160,  $\,$  Y : 160~240 (Note 2):  $C_{re}$  is measured by 3 terminal method with capacitance bridge.

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